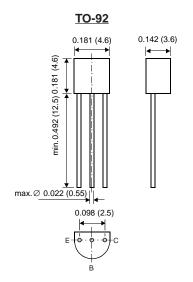
## MPSA06

### **Small Signal Transistors (NPN)**



Dimensions in inches and (millimeters)

#### **FEATURES**

- NPN Silicon Epitaxial Planar Transistor for switching and amplifier applications.
- As complementary type, the PNP transistor MPSA56 is recommended.
- On special request, this transistor is also manufactured in the pin configuration TO-18.
- This transistor is also available in the SOT-23 case with the type designation MMBTA06

#### **MECHANICAL DATA**

Case: TO-92 Plastic Package Weight: approx. 0.18g

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	VCEO	80	V
Emitter-Base Voltage	VEBO	4.0	V
Collector Current	Ic	500	mA
Power Dissipation at TA = 25 °C at Tc = 25 °C	Ptot	625 1.5	mW W
Thermal Resistance Junction to Ambient Air	R <sub>θ</sub> JA	200 <sup>(1)</sup>	K/W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-65 to +150	°C

<sup>1)</sup>Valid provided that leads are kept at ambient temperature



# MPSA06

## **ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	MIN.	.MAX.	UNIT
Collector-Emitter Breakdown Voltage at Ic = 1 mA, IB = 0	V(BR)CEO	80	-	V
Emitter-Base Breakdown Voltage at IE = 100 $\mu$ A, IC = 0	V <sub>(BR)EBO</sub>	4.0	_	V
Collector-Emitter Cutoff Current VCE = 60 V, I <sub>B</sub> = 0	Ices	-	100	nA
Collector-Base Cutoff Current VCB = 80 V, IE = 0	Ісво	_	100	nA
Collector Saturation Voltage at I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA	VCEsat	-	0.25	V
Base-Emitter On Voltage at Ic = 10 mA, IB = 1 mA	VBE(on)	_	1.2	V
DC Current Gain at Vce = 1 V, Ic = 10 mA at Vce = 1 V, Ic = 100 mA	hFE hFE	100 100	_ _ _	- -
Gain-Bandwidth Product at V <sub>CE</sub> = 2.0 V, I <sub>C</sub> = 10 mA, f = 100 MHz	fT	100	_	MHz

<sup>1)</sup> Valid provided that leads are kept at ambient temperature

